

In re Patent Application of:

COFFA ET AL.

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B2
and a biasing device connected to said doped P/N
junction for reverse biasing thereof.

Cancel Claim 29.

B4
38. (Amended) A semiconductor laser device
comprising:
a semiconductor substrate;
a doped P/N junction integrated with said
semiconductor substrate, said P/N junction comprising a
depletion layer and having a shape defining a waveguide, said
depletion layer comprising at least one rare-earth material
for providing a coherent light source; and
a biasing device connected to said doped P/N
junction for reverse biasing thereof.

39. (Amended) A semiconductor laser device according
to Claim 38, wherein said at least one rare-earth material in
the depletion layer of said doped P/N junction forms a base-
collector region for a bipolar transistor.

Cancel Claim 40.

Claims 48-54 have been cancelled without prejudice
to Applicants' right to file a divisional application directed
to the subject matter thereof.